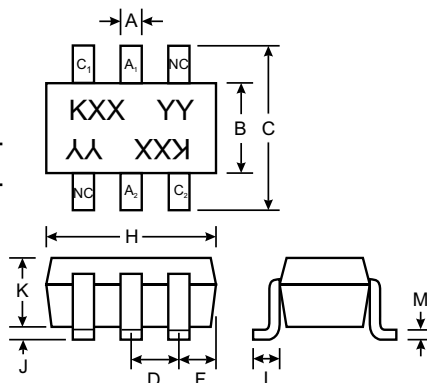


Features

- Planar Die Construction
- 200mW Power Dissipation
- Zener Voltages from 2.4V - 39V
- Ultra-Small Surface Mount Package

Mechanical Data

- Case: SOT-363, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: See Diagram
- Marking: KXX: Part marking (See table page 2)
YY: Date code
- Weight: 0.006 grams (approx.)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
All Dimensions in mm		

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Forward Voltage @ I _F = 10mA	V _F	0.9	V
Power Dissipation (Note 1)	P _d	200	mW
Thermal Resistance, Junction to Ambient Air (Note 1)	R _{θJA}	625	K/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

- Notes:
- Valid provided that device terminals are kept at ambient temperature.
 - V_Z measured @ I_{ZT} using a pulse test. I_{ZT} pulse width = 300μs, period = 5ms.
 - f = 1KHz.

NOTICE

Pin Configuration in our Diodes Incorporated Short Form, page 9-3, printed in September 1999 is in error. Correct Pin Configuration is indicated above.

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Type Number	Marking Code	Zener Voltage Range (Note 2)				Maximum Zener Impedance (Note 3)			Maximum Reverse Current		Temperature Coefficient of Zener Voltage @ I _{ZT} = 5mA mV/°C	
		V _Z @ I _{ZT}			I _{ZT}	Z _{ZT} @ I _{ZT}	Z _{ZK} @ I _{ZK}	I _{ZK}	I _R	V _R		
		Nom (V)	Min (V)	Max (V)	mA	Ω	Ω	mA	uA	V	Min	Max
BZX84C2V4S	KZB	2.4	2.2	2.6	5.0	100	600	1.0	50	1.0	-3.5	0
BZX84C2V7S	KZC	2.7	2.5	2.9	5.0	100	600	1.0	20	1.0	-3.5	0
BZX84C3V0S	KZD	3.0	2.8	3.2	5.0	95	600	1.0	10	1.0	-3.5	0
BZX84C3V3S	KZE	3.3	3.1	3.5	5.0	95	600	1.0	5.0	1.0	-3.5	0
BZX84C3V6S	KZF	3.6	3.4	3.8	5.0	90	600	1.0	5.0	1.0	-3.5	0
BZX84C3V9S	KZG	3.9	3.7	4.1	5.0	90	600	1.0	3.0	1.0	-3.5	0
BZX84C4V3S	KZH	4.3	4.0	4.6	5.0	90	600	1.0	3.0	1.0	-3.5	0
BZX84C4V7S	KZ1	4.7	4.4	5.0	5.0	80	500	1.0	3.0	2.0	-3.5	0.2
BZX84C5V1S	KZ2	5.1	4.8	5.4	5.0	60	480	1.0	2.0	2.0	-2.7	1.2
BZX84C5V6S	KZ3	5.6	5.2	6.0	5.0	40	400	1.0	1.0	2.0	-2.0	-2.5
BZX84C6V2S	KZ4	6.2	5.8	6.6	5.0	10	150	1.0	3.0	4.0	0.4	3.7
BZX84C6V8S	KZ5	6.8	6.4	7.2	5.0	15	80	1.0	2.0	4.0	1.2	4.5
BZX84C7V5S	KZ6	7.5	7.0	7.9	5.0	15	80	1.0	1.0	5.0	2.5	5.3
BZX84C8V2S	KZ7	8.2	7.7	8.7	5.0	15	80	1.0	0.7	5.0	3.2	6.2
BZX84C9V1S	KZ8	9.1	8.5	9.6	5.0	15	100	1.0	0.5	6.0	3.8	7.0
BZX84C10S	KZ9	10	9.4	10.6	5.0	20	150	1.0	0.2	7.0	4.5	8.0
BZX84C11S	KY1	11	10.4	11.6	5.0	20	150	1.0	0.1	8.0	5.4	9.0
BZX84C12S	KY2	12	11.4	12.7	5.0	25	150	1.0	0.1	8.0	6.0	10.0
BZX84C13S	KY3	13	12.4	14.1	5.0	30	170	1.0	0.1	8.0	7.0	11.0
BZX84C15S	KY4	15	13.8	15.6	5.0	30	200	1.0	0.1	10.5	9.2	13.0
BZX84C16S	KY5	16	15.3	17.1	5.0	40	200	1.0	0.1	11.2	10.4	14.0
BZX84C18S	KY6	18	16.8	19.1	5.0	45	225	1.0	0.1	12.6	12.4	16.0
BZX84C20S	KY7	20	18.8	21.2	5.0	55	225	1.0	0.1	14.0	14.4	18.0
BZX84C22S	KY8	22	20.8	23.3	5.0	55	250	1.0	0.1	15.4	16.4	20.0
BZX84C24S	KY9	24	22.8	25.6	5.0	70	250	1.0	0.1	16.8	18.4	22.0
BZX84C27S	KYA	27	25.1	28.9	2.0	80	300	0.5	0.1	18.9	21.4	25.3
BZX84C30S	KYB	30	28.0	32.0	2.0	80	300	0.5	0.1	21.0	24.4	29.4
BZX84C33S	KYC	33	31.0	35.0	2.0	80	325	0.5	0.1	23.1	27.4	33.4
BZX84C36S	KYD	36	34.0	38.0	2.0	90	350	0.5	0.1	25.2	30.4	37.4
BZX84C39S	KYE	39	37.0	41.0	2.0	130	350	0.5	0.1	27.3	33.4	41.2

Notes: 1. Valid provided that device terminals are kept at ambient temperature.
2. V_Z measured @ I_{ZT} using a pulse test. I_{ZT} pulse width = 300μs, period = 5ms.
3. f = 1KHz.

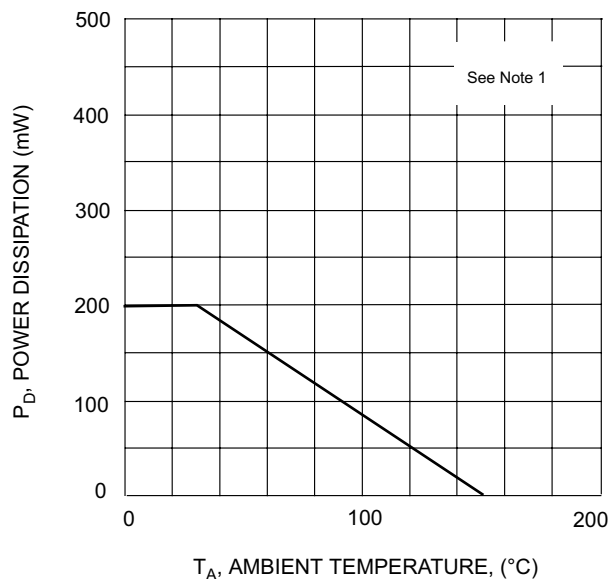


Fig. 1. Power Derating Curve

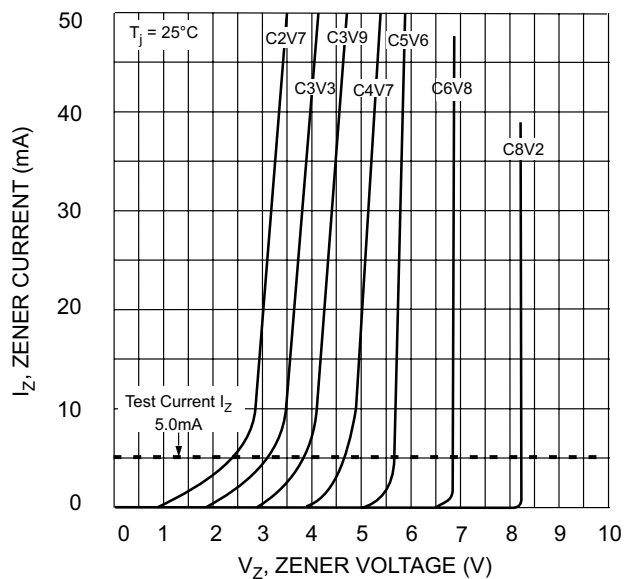


Fig. 2. Zener Breakdown Characteristics

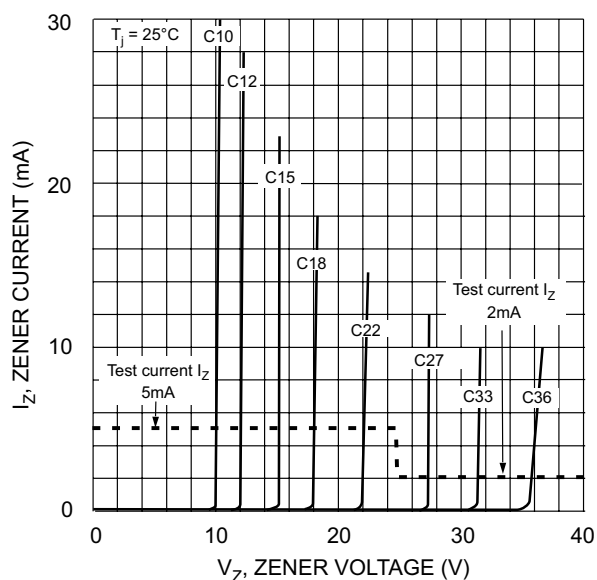


Fig. 3. Zener Breakdown Characteristics

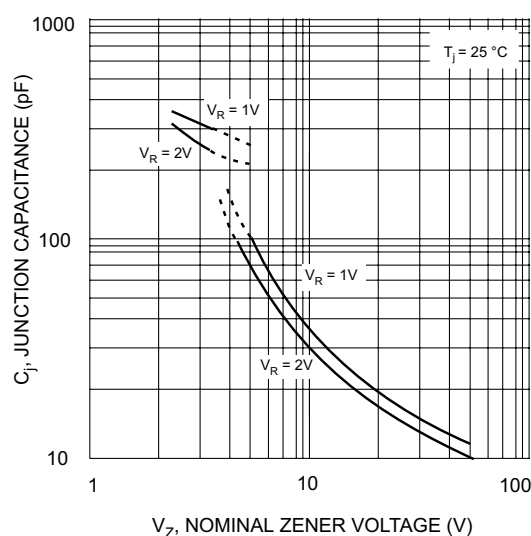


Fig. 4. Junction Capacitance vs. Nominal Zener Voltage